P-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	-30 V
● I_D	-10 A
● $R_{DS(ON)}$(at V_{GS}=-10V)	19 mΩ
● $R_{DS(ON)}$(at V_{GS}=-4.5V)	28 mΩ
● 100% EAS Tested	

General Description

- Trench Power LV MOSFET technology
- High density cell design for Low RDS(ON)
- High Speed switching
- Moisture Sensitivity Level 3
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings (T_A=25 unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-30	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_A=25	I_D	-10	A
	T_A=100		-6.3	
Pulsed Drain Current [A]		I_{DM}	-80	A
Avalanche energy [B]		EAS	56	mJ
Total Power Dissipation [C]	T_A=25	P_D	2.5	W
	T_A=100		1	
Junction and Storage Temperature Range		T_J ,T_{STG}	-55 +150	

■Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient [D]	Steady-State	$R_{\theta JA}$	40	50	/W

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	

■ Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units

Static Parameter

SOP-8 Package information

SYMBOL	MIN.		
	0.053	0.069	
B	0.004	0.010	
		0.061	
D		0.020	
E			
F			
G	0.050BSC		1.270BSC
H			
J			
K			

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical